

isc N-Channel MOSFET Transistor

2SK2611

DESCRIPTION

- Drain Current  $-I_D=9A@ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}= 900V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

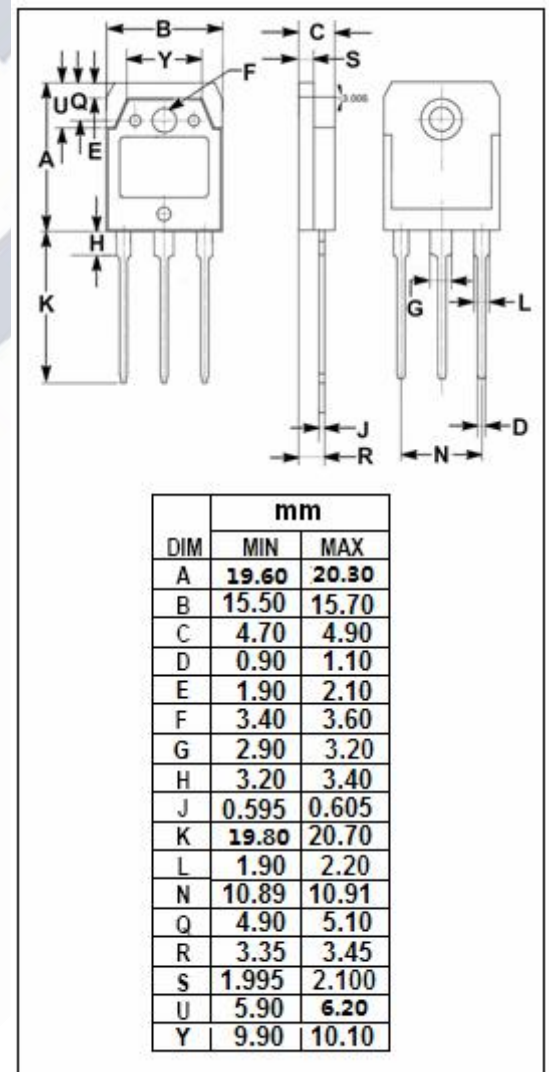
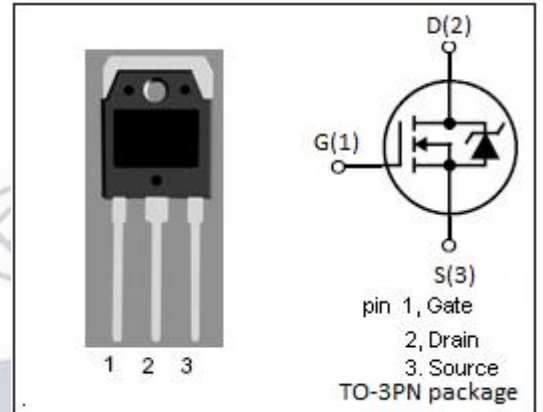
- low on-resistance.
- High speed switching.
- No secondary breakdown.
- Suitable for switching regulator, DC-DC control.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	900	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $TC=25^\circ C$	9	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ C$	150	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	0.833	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	50	$^\circ C/W$



**isc N-Channel Mosfet Transistor****2SK2611****• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 10mA	900			V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> = 1mA	2.0		4.0	V
R <sub>DS(ON)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 4A			1.4	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			±10	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =720V; V <sub>GS</sub> = 0			100	uA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>F</sub> = 9A; V <sub>GS</sub> =0			1.9	V